

FDMC6890NZ

Dual N-Channel PowerTrench® MOSFET

20V, 4A, Q1:68mΩ, Q2:100mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 68mΩ at V_{GS} = 4.5V, I_D = 4A
- Max $r_{DS(on)}$ = 100mΩ at V_{GS} = 2.5V, I_D = 3A

Q2: N-Channel

- Max $r_{DS(on)}$ = 100mΩ at V_{GS} = 4.5V, I_D = 4A
- Max $r_{DS(on)}$ = 150mΩ at V_{GS} = 2.5V, I_D = 2A
- Low gate Charge
- RoHS Compliant

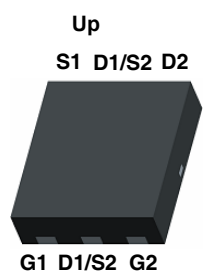


General Description

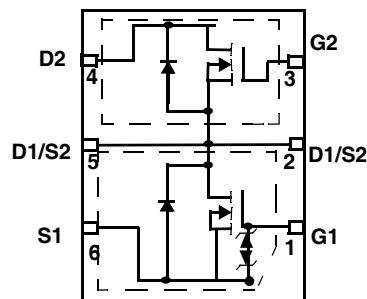
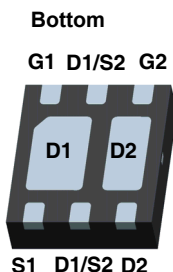
FDMC6890NZ is a compact single package solution for DC to DC converters with excellent thermal and switching characteristics. Inside the Power 33 package features two N-channel MOSFETs with low on-state resistance and low gate charge to maximize the power conversion and switching efficiency. The Q1 switch also integrates gate protection from unclamped voltage input.

Application

- DC - DC Conversion



Power 33



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V _{DS}	Drain to Source Voltage	20	20	V
V _{GS}	Gate to Source Voltage	±12	±12	V
I _D	-Continuous	4		A
	-Pulsed	10		
P _D	Power Dissipation (Steady State) Q1 (Note 1a)	1.92		W
	Power Dissipation (Steady State) Q2	1.78		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	Q1 (Note 1a)	65	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	Q2	70	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
6890N	FDMC6890NZ	Power 33	7inch	8mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	Q1 Q2	20 20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C	Q1 Q2		13 12		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{V}$, $V_{GS} = 0\text{V}$	Q1 Q2			1 1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{V}$, $V_{DS} = 0\text{V}$	Q1 Q2			± 10 ± 100	μA nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	Q1 Q2	0.6 0.6	0.9 1.0	2 2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C	Q1 Q2		-3 -3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5\text{V}$, $I_D = 4\text{A}$ $V_{GS} = 2.5\text{V}$, $I_D = 3\text{A}$	Q1		58 77	68 100	m Ω
		$V_{GS} = 4.5\text{V}$, $I_D = 4\text{A}$ $V_{GS} = 2.5\text{V}$, $I_D = 2\text{A}$	Q2		67 102	100 150	
g_{FS}	Forward Transconductance	$V_{DS} = V$, $I_D = 4\text{A}$	Q1 Q2		10 7		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	Q1 Q2		205 190	270 250	pF
C_{oss}	Output Capacitance		Q1 Q2		60 60	80 80	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		40 35	60 55	pF
R_g	Gate Resistance	$f = 1\text{MHz}$	Q1 Q2		3.3 2.8		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{V}$, $I_D = 4\text{A}$, $R_{GEN} = 6\Omega$	Q1 Q2		4 4	10 10	ns
t_r	Rise Time		Q1 Q2		13 12	22 21	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		10 7	19 14	ns
t_f	Fall Time		Q1 Q2		6 6	12 12	ns
$Q_{g(TOT)}$	Total Gate Charge at 4.5V	$V_{GS} = 0\text{V}$ to 4.5V	Q1 Q2		2.4 1.8	3.4 2.6	nC
$Q_{g(2)}$	Total Gate Charge at 2V	$V_{DD} = 10\text{V}$ $I_D = 4\text{A}$	Q1 Q2		1.4 0.6	1.9 0.8	nC
Q_{gs}	Gate to Source Gate Charge		Q1 Q2		0.4 0.5		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		0.9 0.8		nC

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

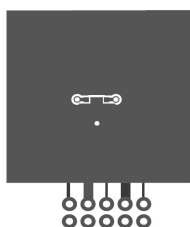
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Drain-Source Diode Characteristics

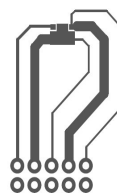
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 4\text{A}$	Q1 Q2		0.94 0.92	1.25 1.25	V
t_{rr}	Reverse Recovery Time	$I_F = 4\text{A}, di/dt = 100\text{A/s}$	Q1 Q2		18 17	27 26	ns
Q_{rr}	Reverse Recovery Charge		Q1 Q2		9 10	14 15	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 65°C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 150°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width $< 300\mu\text{s}$, Duty cycle $< 2.0\%$.

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

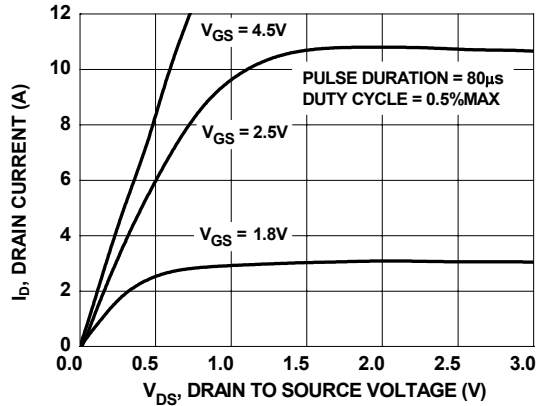


Figure 1. On-Region Characteristics

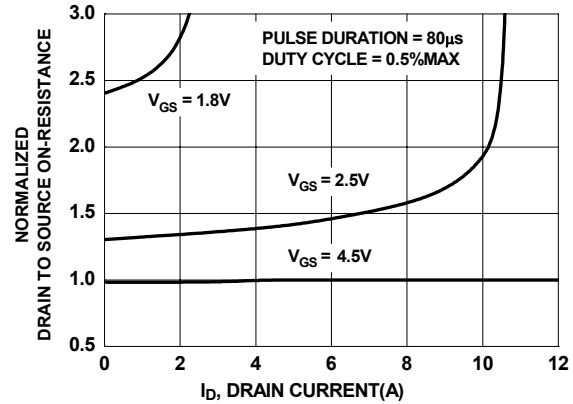


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

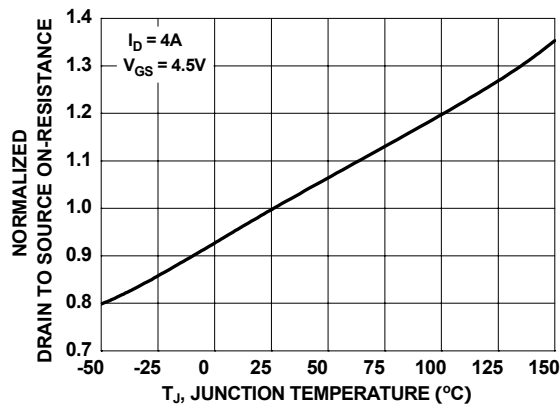


Figure 3. Normalized On -Resistance vs Junction Temperature

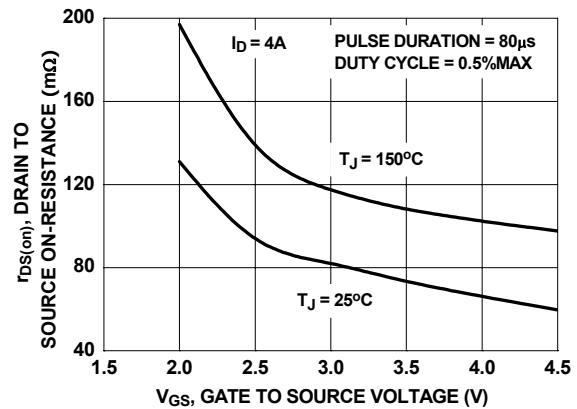


Figure 4. On-Resistance vs Gate to Source Voltage

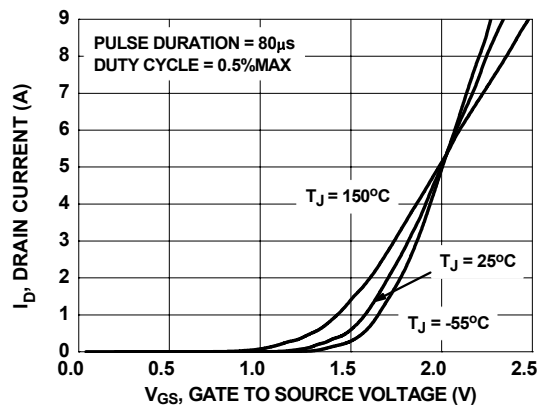


Figure 5. Transfer Characteristics

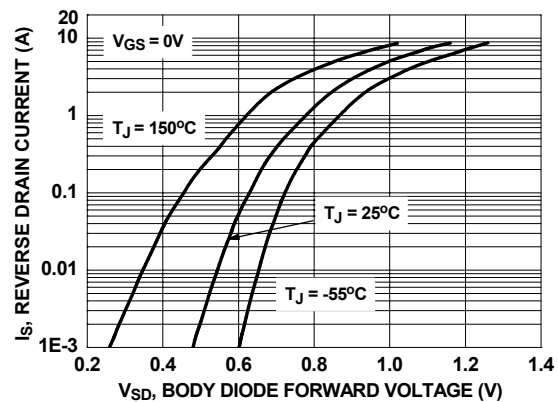


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

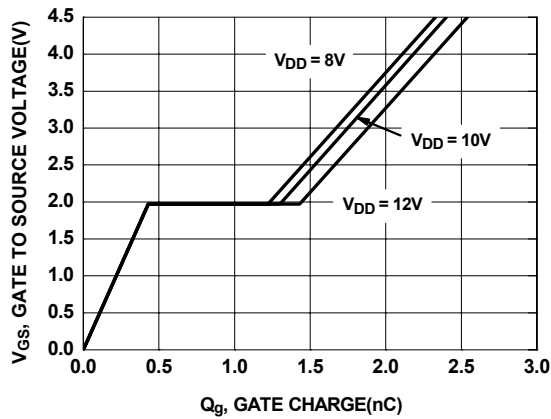


Figure 7. Gate Charge Characteristics

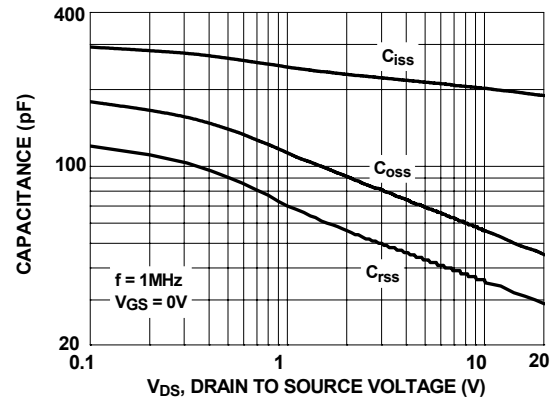


Figure 8. Capacitance vs Drain to Source Voltage

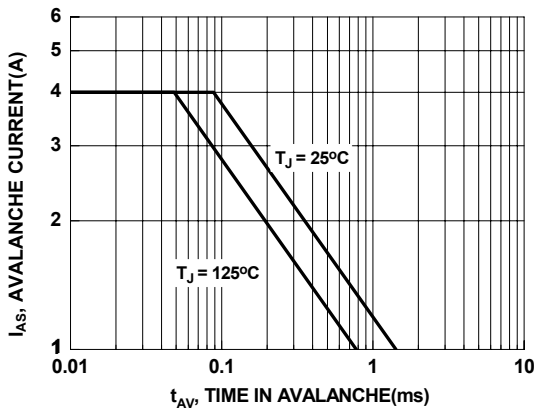


Figure 9. Unclamped Inductive Switching Capability

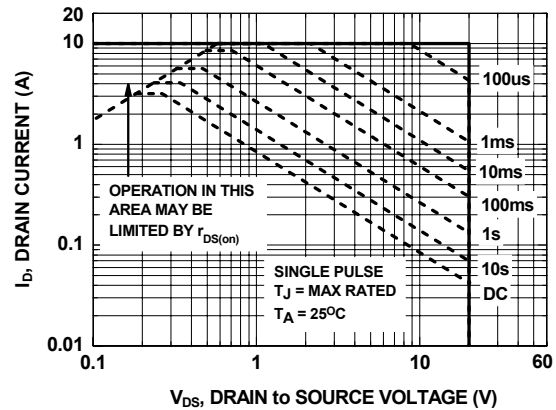


Figure 10. Forward Bias Safe Operating Area

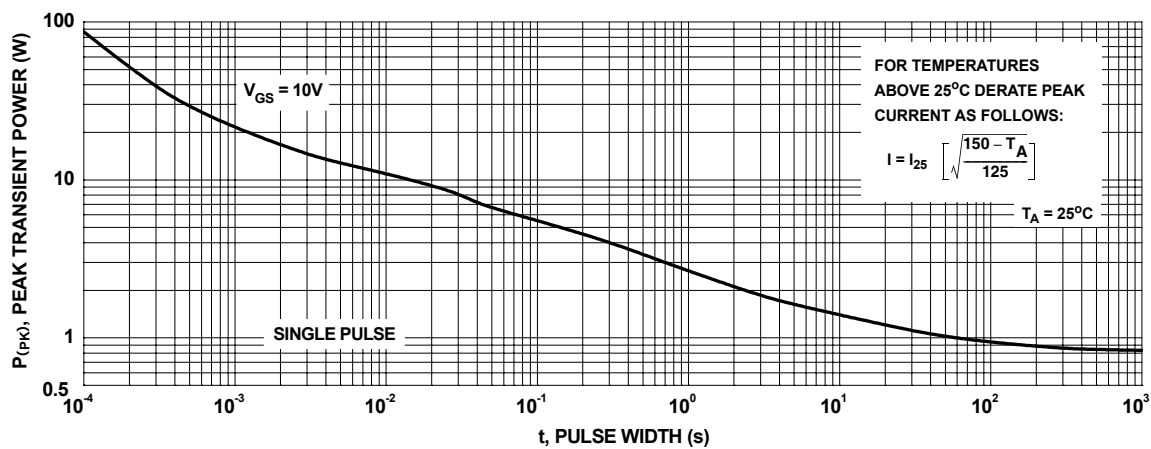
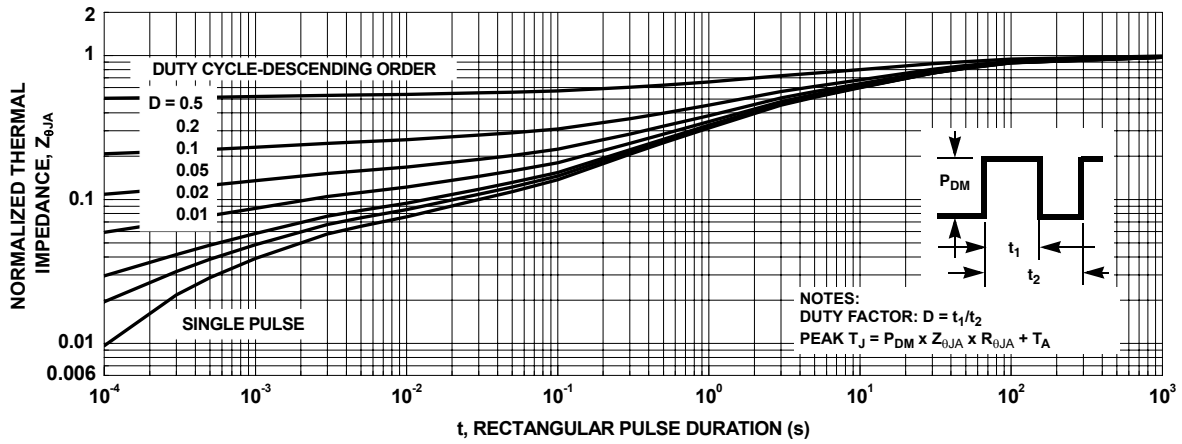


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted



Typical Characteristics (Q2 N-Channel)

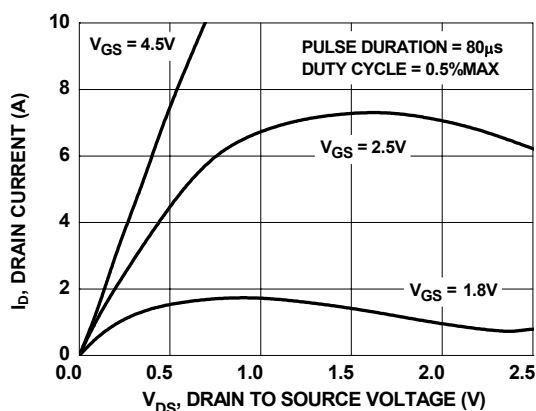


Figure 13. On Region Characteristics

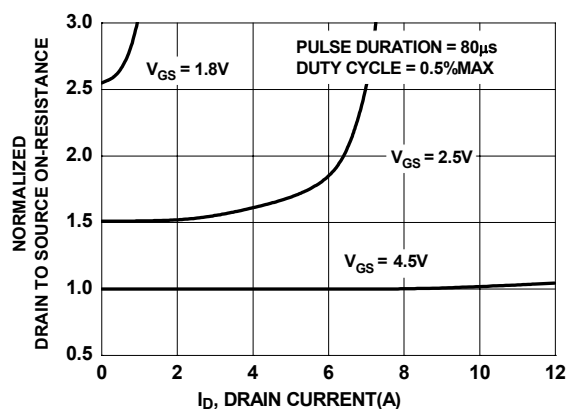


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

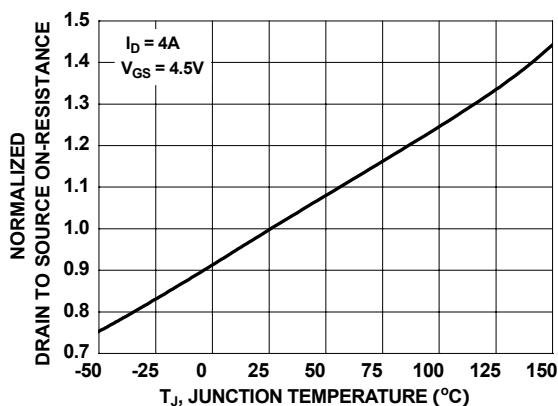


Figure 15. Normalized On Resistance vs Junction Temperature

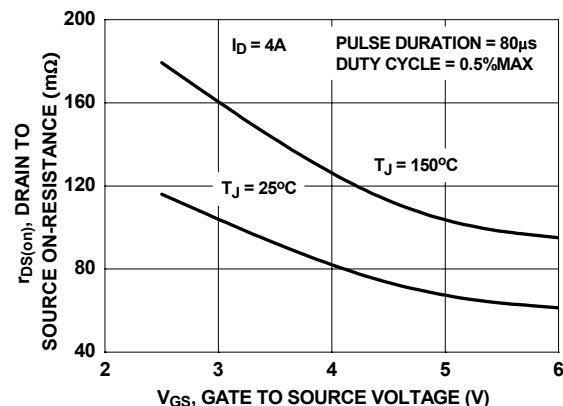


Figure 16. On-Resistance vs Gate to Source Voltage

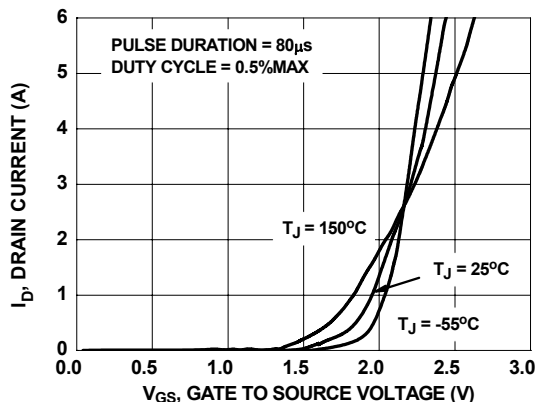


Figure 17. Transfer Characteristics

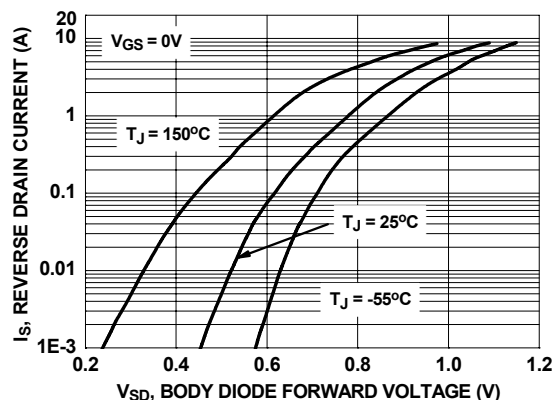


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics

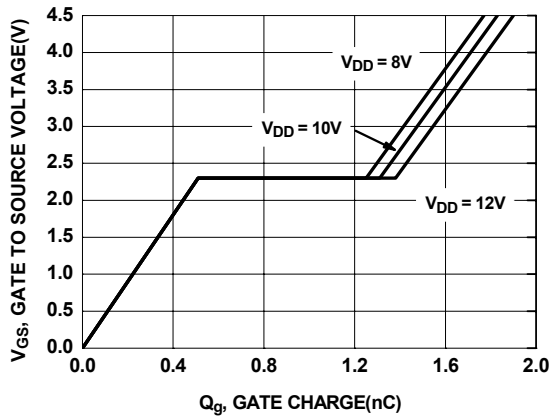


Figure 19. Gate Charge Characteristics

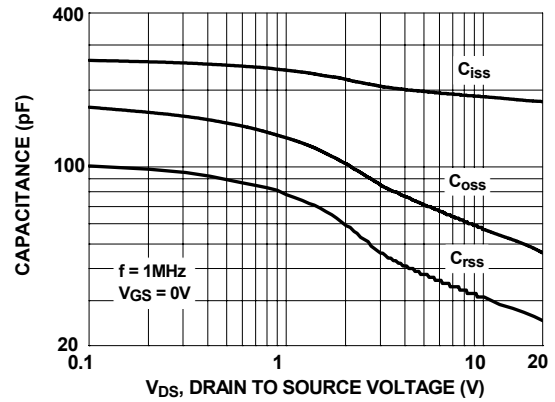


Figure 20. Capacitance vs Drain to Source Voltage

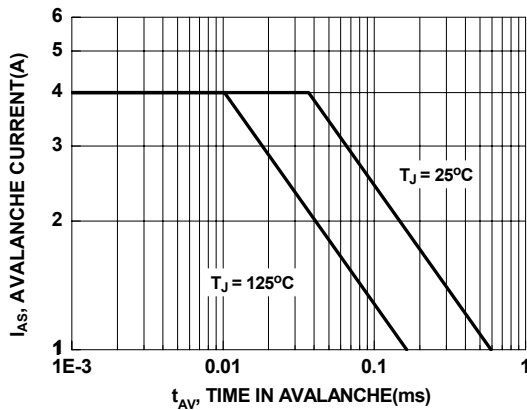


Figure 21. Unclamped Inductive Switching Capability

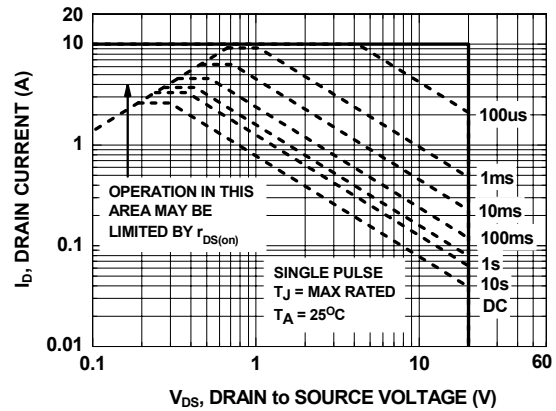


Figure 22. Forward Bias Safe Operating Area

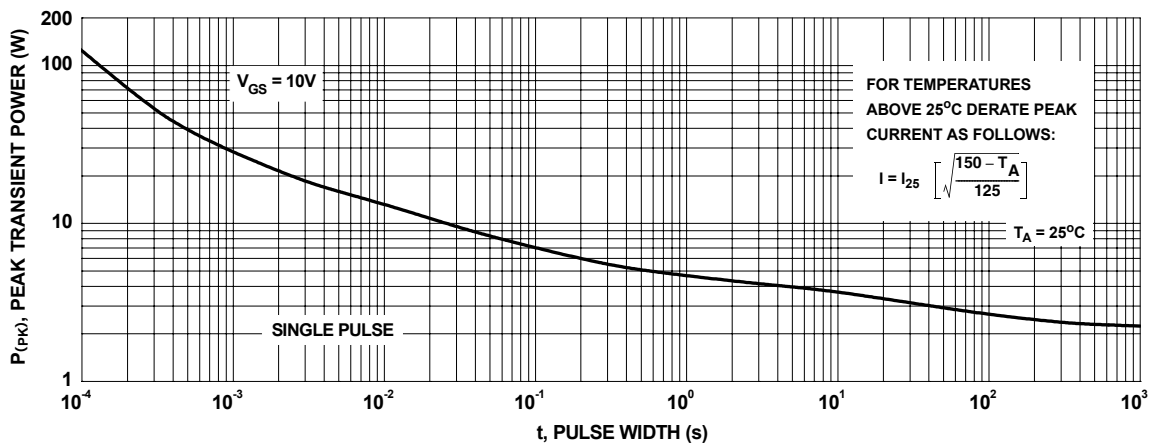


Figure 23. Single Pulse Maximum Power Dissipation

Typical Characteristics

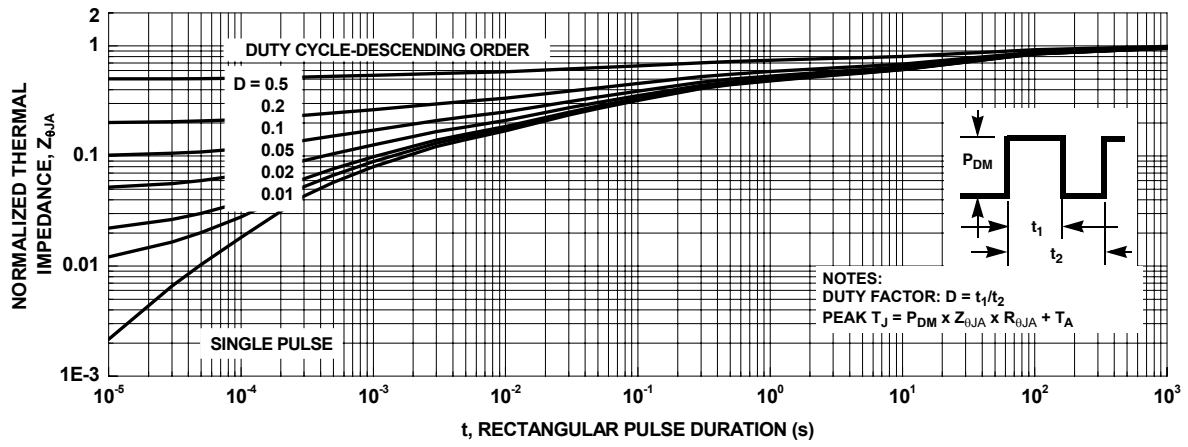
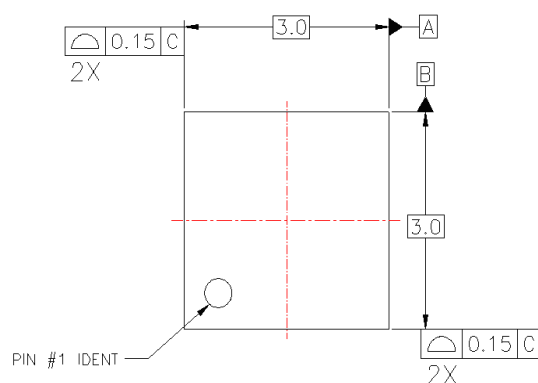
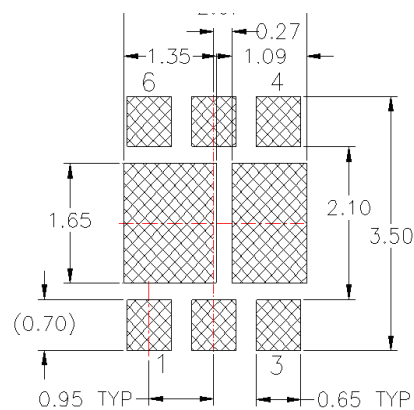


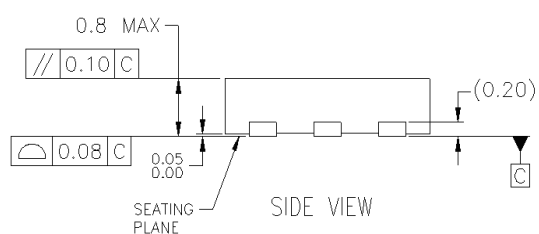
Figure 24. Transient Thermal Response Curve



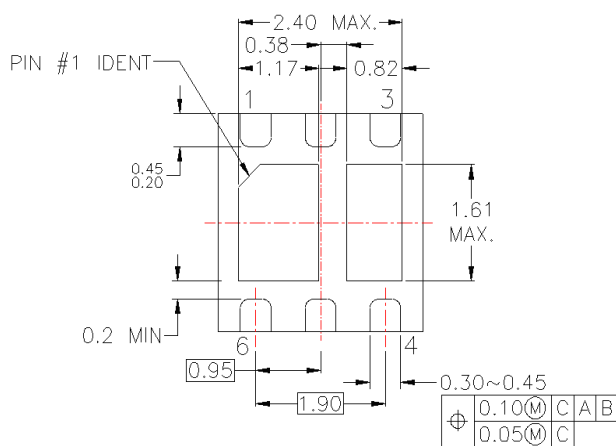
TOP VIEW



RECOMMENDED LAND PATTERN



SIDE VIEW



BOTTOM VIEW

NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-229,
VARIATION WEEA, DATED 11/2001
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER
ASME Y14.5M, 1994

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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